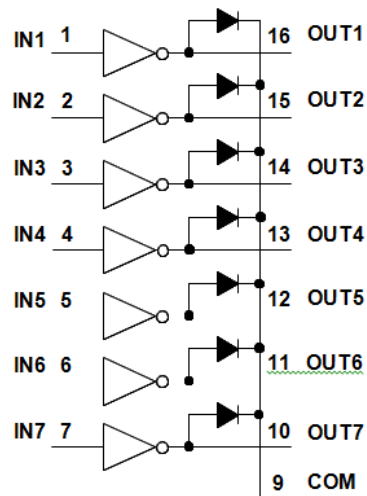
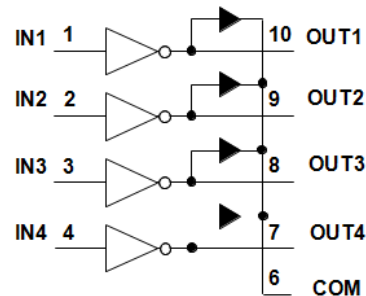


Functional Diagram



ULN2003V12

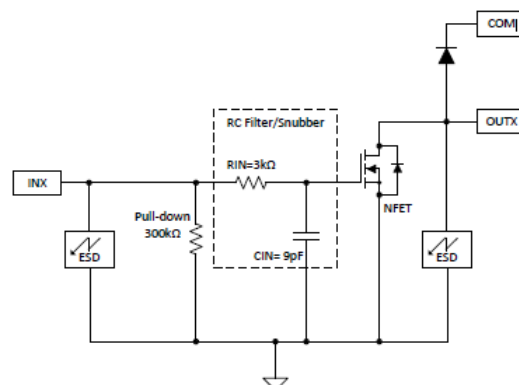


ULN2003F12

Pin Descriptions

Pin Name	Package Number			Description
	SO16	TSSOP16	DFN3030-10	
IN1 ~ IN7	1~7	1~7	1~4	Logic Input Pins IN1 through IN7
GND	8	8	5	Ground Reference Pin
COM	9	9	6	Internal Free-Wheeling Diode Common Cathode Pin
OUT7 ~ OUT1	10~16	10~16	7~10	Channel Output Pins OUT7 through OUT1

Functional Block Diagram (Single Channel)



Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Symbol	Parameter	Rating		Unit
		Min	Max	
V_{IN}	Pin2 IN1~IN7 to GND Voltage	-0.3	5.5	V
V_{OUT}	Pins OUT1~OUT7 to GND Voltage	—	20	V
V_{COM}	Pin COM to GND Voltage	—	20	V
I_{GND}	Max GND-Pin Continuous Current ($+100^\circ\text{C} < T_J < +125^\circ\text{C}$)	—	700	mA
	Max GND-Pin Continuous Current ($T_J < +100^\circ\text{C}$)	—	1.0	A
P_D	Total Device Power Dissipation at $T_A = +85^\circ\text{C}$	16 Pin – SOIC	0.412	W
		16 Pin – TSSOP	0.277	W
		10 Pin – DFN3030	0.615	W
θ_{JA}	Thermal Resistance Junction-to-Ambient (Note 6)	16 Pin – SOIC	97	$^\circ\text{C/W}$
		16 Pin – TSSOP	144	
		10 Pin – DFN3030	65	
θ_{JC}	Thermal Resistance Junction-to-Case (Note 7)	16 Pin – SOIC	41	$^\circ\text{C/W}$
		16 Pin – TSSOP	61	
		10 Pin – DFN3030	17	
ESD	HBM	—	4	kV
	CDM	—	1	kV
T_J	Junction Temperature	-55	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55	150	$^\circ\text{C}$

- Notes:
- Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
 - All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.
 - Maximum power dissipation is a function of $T_J(\text{max})$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(\text{max}) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of $+150^\circ\text{C}$ can affect reliability.
 - Maximum power dissipation is a function of $T_J(\text{max})$, θ_{JC} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(\text{max}) - T_C)/\theta_{JA}$. Operating at the absolute maximum T_J of $+150^\circ\text{C}$ can affect reliability.

Recommended Operating Conditions (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit
V_{OUT}	Channel Off-Stage Output Pull-Up Voltage	—	—	V
V_{COM}	COM Pin Voltage	—	—	V
$I_{OUT(ON)}$	Per Channel Continuous Sink Current	$V_{INx} = 3.3\text{V}$	—	mA
		$V_{INx} = 5.0\text{V}$	—	
T_J	Operating Junction Temperature	-40	—	$^\circ\text{C}$

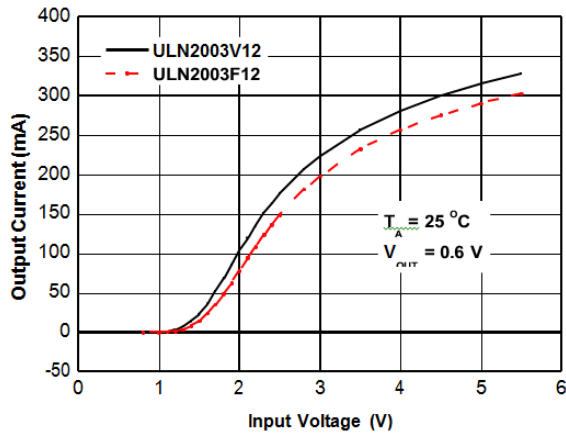
Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Specified over the recommended junction temperature range $T_J = -40^\circ\text{C}$ to $+125^\circ\text{C}$ and over recommended operating conditions unless otherwise noted. Typical values are at $T_J = +25^\circ\text{C}$.

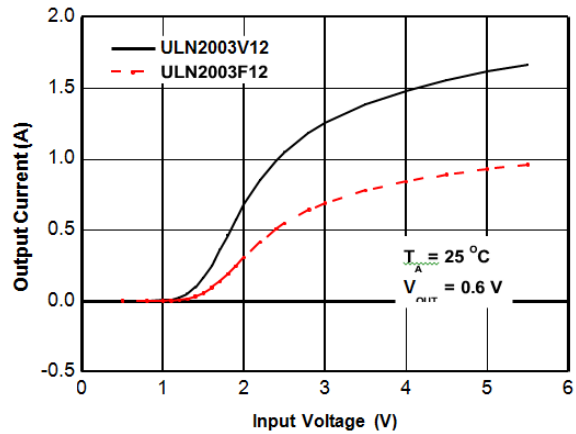
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
INPUTS IN1 THROUGH IN7 PARAMETERS						
$V_{I(on)}$	IN1~IN7 logic high input voltage	$V_{CE} = 2\text{V}$, $I_C = 300\text{mA}$	1.65	—	—	V
$V_{I(off)}$	IN1~IN7 logic low input voltage	$I_I = 250\mu\text{A}$, $I_C = 100\text{mA}$	—	—	0.6	V
$I_{I(on)}$	IN1~IN7 ON state input current	$I_F = 350\text{mA}$	—	12	25	μA
$I_{I(off)}$	IN1~IN7 OFF state input leakage	—	—	—	250	nA
OUTPUTS OUT1 THROUGH OUT7 PARAMETERS						
$V_{OL(vce-sat)}$	OUT1~OUT7 low-level output voltage	$V_{INX} = 3.3\text{V}$, $I_{OUTX} = 20\text{mA}$	—	0.12	0.15	V
		$V_{INX} = 3.3\text{V}$, $I_{OUTX} = 100\text{mA}$	—	0.6	0.75	
		$V_{INX} = 5.0\text{V}$, $I_{OUTX} = 20\text{mA}$	—	0.09	0.11	
		$V_{INX} = 5.0\text{V}$, $I_{OUTX} = 140\text{mA}$	—	0.6	0.75	
$I_{OUT(on)}$	OUT1~OUT7 ON-state continuous current at $V_{OUTX} = 0.6\text{V}$	$V_{INX} = 3.3\text{V}$, $V_{OUTX} = 0.6\text{V}$	80	100	—	V
		$V_{INX} = 5.0\text{V}$, $V_{OUTX} = 0.6\text{V}$	80	140	—	A
$I_{OUT(off)}$	OUT1~OUT7 OFF-state leakage current	$V_{INX} = 0\text{V}$, $V_{OUTX} = V_{COM} = 16\text{V}$	—	0.5	—	μA
SWITCHING PARAMETERS						
t_{PHL}	OUT1~OUT7 logic high propagation delay	$V_{INX} = 3.3\text{V}$, $V_{pull-up} = 12\text{V}$, $R_{pull-up} = 1\text{k}\Omega$	—	50	70	ns
t_{PLH}	OUT1~OUT7 logic low propagation delay	$V_{INX} = 3.3\text{V}$, $V_{pull-up} = 12\text{V}$, $R_{pull-up} = 1\text{k}\Omega$	—	121	140	ns
$t_{CHANNEL}$	Channel-to-channel delay	Over recommended operating conditions and with same test conditions on channels.	—	15	50	ns
R_{PD}	IN1~IN7 input pull-down resistance	—	210k	300k	390k	Ω
ζ	IN1~IN7 input filter time constant	—	—	9	—	ns
C_{OUT}	OUT1~OUT7 output capacitance	$V_{INX} = 3.3\text{V}$, $V_{OUTX} = 0.4\text{V}$	—	15	—	pF
FREE-WHEELING DIODE PARAMETERS						
V_F	Forward voltage drop	$I_{F-peak} = 140\text{mA}$, $V_F = V_{OUTX} - V_{COM}$	—	1.2	—	V
I_{F-peak}	Diode peak forward current	—	—	140	—	mA

Performance Characteristics

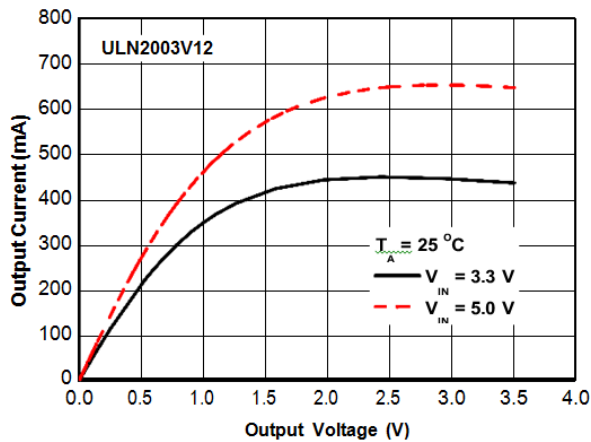
Output Current vs. Input Voltage (One Darlington)



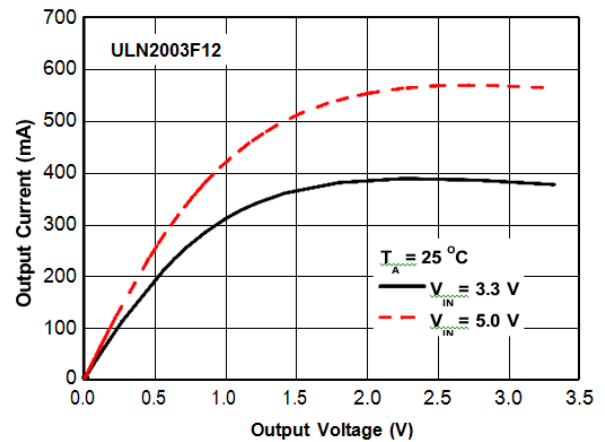
Output Current vs. Input Voltage (All Darlingtons in Parallel)



Output Current vs. Output Voltage

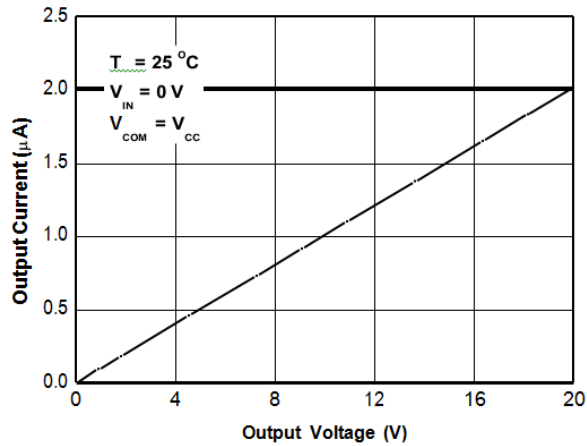


Output Current vs. Output Voltage

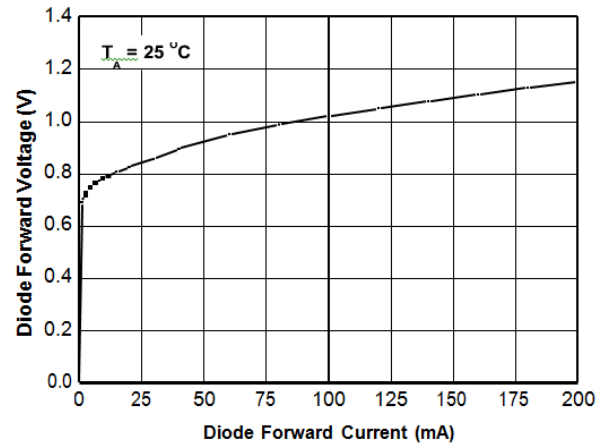


Performance Characteristics (continued)

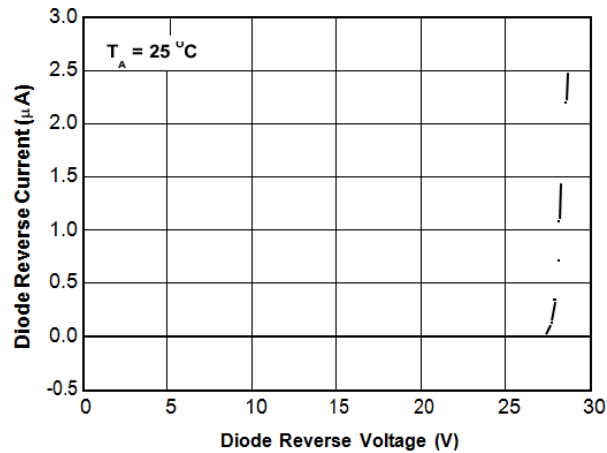
Output Current vs. Output Voltage



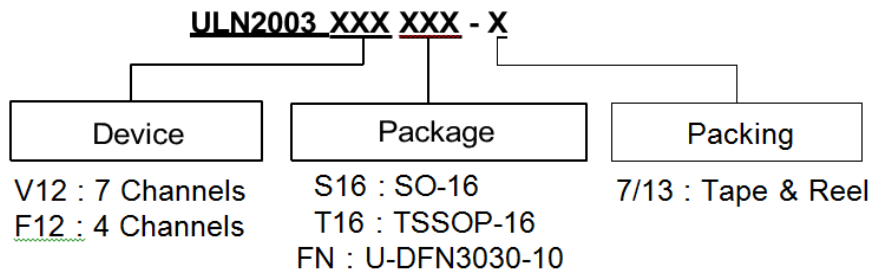
Diode Forward Voltage vs. Diode Forward Current



Diode Reverse Current vs. Diode Reverse Voltage



Ordering Information

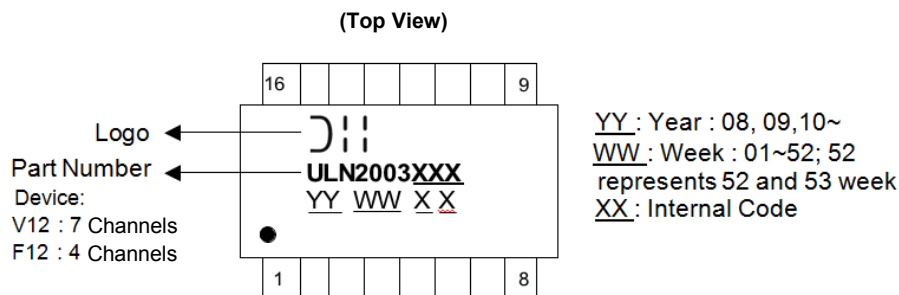


Device	Package Code	Packaging (Note 8)	7"/13" Tape and Reel	
			Quantity	Part Number Suffix
ULN2003V12S16-13	S16	SO-16	2,500/Tape & Reel	-13
ULN2003V12T16-13	T16	TSSOP-16	2,500/Tape & Reel	-13
ULN2003F12FN-7	FN	DFN3030-10	3,000/Tape & Reel	-7

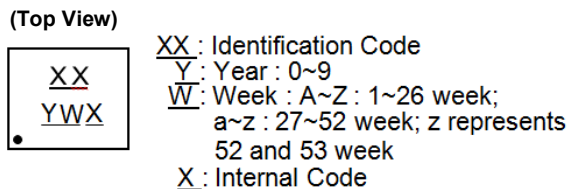
Note: 8. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

(1) SO-16 and TSSOP-16



(2) DFN3030-10

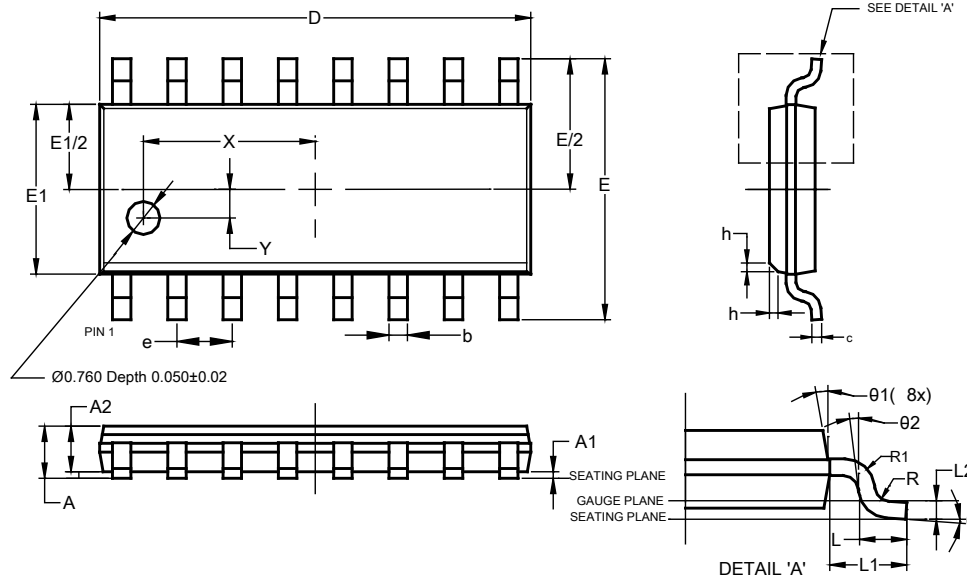


Part Number	Package	Identification Code
ULN2003F12FN-7	DFN3030-10	A3

Package Outline Dimensions

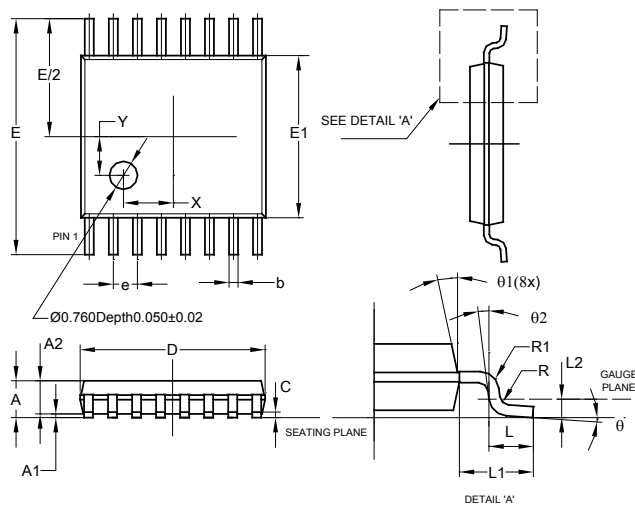
Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-16



SO-16			
Dim	Min	Max	Typ
A	--	1.260	--
A1	0.10	0.23	--
A2	1.02	--	--
b	0.31	0.51	--
c	0.10	0.25	--
D	9.80	10.00	--
E	5.90	6.10	--
E1	3.80	4.00	--
e	1.27 BSC		
h	0.15	0.25	0.20
L	0.40	1.27	--
L1	1.04 REF		
L2	0.25 BSC		
R	0.07	--	--
R1	0.07	--	--
X	3.945 REF		
Y	0.661 REF		
theta	0°	8°	--
theta1	5°	15°	--
theta2	0°	--	--
All Dimensions in mm			

TSSOP-16

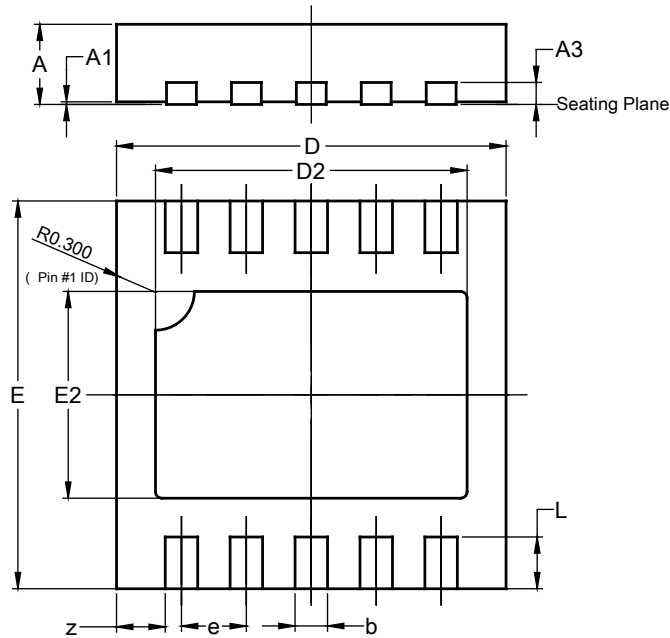


TSSOP-16			
Dim	Min	Max	Typ
A	-	1.08	-
A1	0.05	0.15	-
A2	0.80	0.93	-
b	0.19	0.30	-
c	0.09	0.20	-
D	4.90	5.10	-
E	6.40 BSC		
E1	4.30	4.50	-
e	0.65 BSC		
L	0.45	0.75	-
L1	1.00 REF		
L2	0.25 BSC		
R / R1	0.09	-	-
X	-	-	1.350
Y	-	-	1.050
theta	0°	8°	-
theta1	5°	15°	-
theta2	0°	-	-
All Dimensions in mm			

Package Outline Dimensions (continued)

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN3030-10

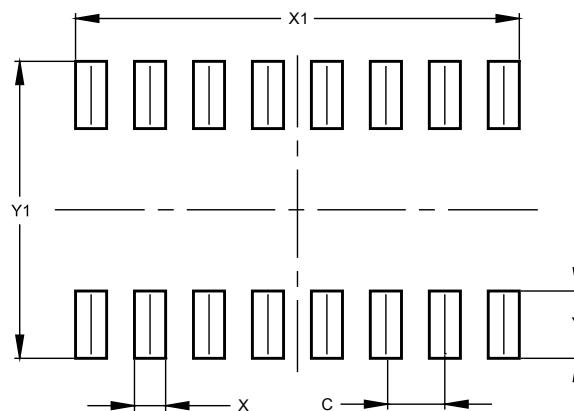


U-DFN3030-10			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.02
A3	—	—	0.15
b	0.20	0.30	0.25
D	2.90	3.10	3.00
D2	2.30	2.50	2.40
E	2.90	3.10	3.00
E2	1.50	1.70	1.60
e	—	—	0.50
L	0.25	0.55	0.40
z	—	—	0.375
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-16

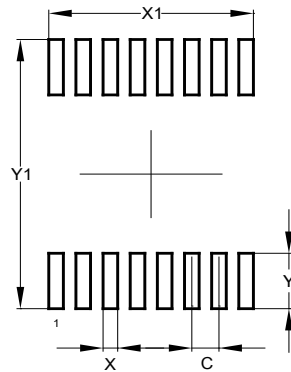


Dimensions	Value (in mm)
C	1.270
X	0.670
X1	9.560
Y	1.450
Y1	6.400

Suggested Pad Layout (continued)

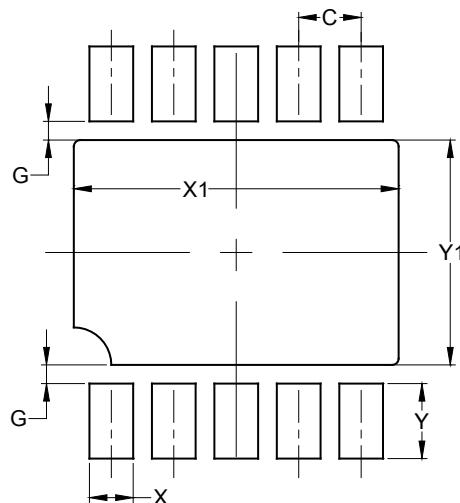
Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSSOP-16



Dimensions	Value (in mm)
C	0.650
X	0.350
X1	4.900
Y	1.400
Y1	6.800

U-DFN3030-10



Dimensions	Value (in mm)
C	0.50
G	0.15
X	0.35
X1	2.60
Y	0.60
Y1	1.80

Mechanical Data

- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals:
 - SO-16** and **TSSOP-16**: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ③
 - DFN3030-10**: Finish NiPdAu over Copper Lead-Frame, Solderable per MIL-STD-202, Method 208 ③
- Weight:
 - SO-16**: 0.129 grams (Approximate)
 - TSSOP-16**: 0.055 grams (Approximate)
 - DFN3030-10**: 0.016 grams (Approximate)

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